PCN Number: 2			20	20230707001.2				PCN Date:		ate:	July 07, 2023			
Title: Cu bond wire Qualification plus reel dimension change and Qualification of RFAB a an additional fab site for select devices									fication of RFAB as					
Cus	tomer	Contac	t: C	Char	nge Mai	nagei	ment team	Dept	::	Ç)ua	ity Sei	rvices	
Proposed 1 st Ship Date: Jan 3,			Jan 3,	2024	Sample requests accepted until:			Aug 7, 2023						
*Sa	*Sample requests received after July 7, 2023 will not be supported.													
Cha	nge Ty	pe:												
	Assen	nbly Site	е				Design					Wafer Bump Material		
\boxtimes	Assen	nbly Pro	cess				Data Sheet					Wafe	r Bump Process	
\boxtimes	Assen	nbly Mat	terials				Part number	char	nge		X	Wafe	r Fab Site	
				n		Test Site				\boxtimes	Wafe	r Fab Material		
□ Packing/Shipping/Labeling					Test Process	;				Wafe	r Fab Process			
	PCN Details													
Des	Description of Change:													

Texas Instruments is pleased to announce the additional Assembly BOM options plus reel dimension changes and qualification of its RFAB fabrication facility as an additional Wafer Fab source for the list of devices in the "Product Affected" section below..

С	urrent Fab Site	•	Additional Fab Site			
Current Fab Process Site		Wafer Diameter	Additional Fab Site	Process	Wafer Diameter	
MIHO8	LBC7	200 mm	RFAB	LBC7	300 mm	

Construction differences for Group 2 & 3 are as follows:

What	Current	Additional		
Current Bond wire,	Die to LF: 1mil Cu or 0.96 Au	Die to LF: 0.8 mil Cu		
Diameter	Die to Die: 0.96 mil Au	Die to Die: 0.8 mil Cu		

Additionally, below only applies to Group 3:

What	From	То
Reel Width	24.4 mm	16.4 mm
Carrier Tape Width	24 mm	16 mm

Qual details are provided in the Qual Data Section.

Reason for Change:

Continuity of Supply

Anticipated impact on Form, Fit, Function, Quality or Reliability (positive / negative):

None

Impact on Environmental Ratings:

Checked boxes indicate the status of environmental ratings following implementation of this change. If below boxes are checked, there are no changes to the associated environmental ratings.

RoHS	REACH	Green Status	IEC 62474
No Change	⊠ No Change	☑ No Change	⊠ No Change

Changes to product identification resulting from this PCN:

Fab Site Information:

Chip Site	Chip Site Origin Code (20L)	Chip Site Country Code (21L)	Chip Site City Ibaraki	
MIHO8	MH8	JPN		
RFAB	RFB	USA	Richardson	

Sample product shipping label (not actual product label)

TEXAS INSTRUMENTS

MADE IN: Malaysia
2DC: 20:

MSL 2 /260C/1 YEAR SEAL DT

MSL '2 /260C/1 YEAR SEAL DT MSL 1 /235C/UNLIM 03/29/04 OPT:

175. 1750 LBL: 5A (L)TO:1750



(1P) \$N74L\$07N\$R (Q) 2000 (D) 0336 (31T)LOT: 3959047MLA (4W) TKY(1T) 7523483\$12 (P) (2P) REV: (V) 0033317

(2É) REV: (V) 0033317 (20L) CSO: SHE (21L) CCO:USA (22L) ASO: MLA (23L) ACO: MYS

Product Affected:

ISO5451QDWQ1	ISO5851QDWQ1	ISO5452QDWRQ1	ISO5852SQDWQ1
ISO5452QDWQ1	ISO5451QDWRQ1	ISO5851QDWRQ1	ISO5852SQDWR0

Group 2 device list – Cu Wire only:

UCC21520QDWQ1	UCC21520AQDWQ1	UCC21320QDW KRQ1	UCC21530QDWK
SN21530QDWKRQ1	UCC21520QDWRQ1	UCC21520AQDWRQ1	UCC21530BQDWI
UCC21320QDWKQ1	UCC21530QDWKQ1	UCC21530BQDWKQ1	

Group 3 device list – Cu Wire & Reel diameter only:

ISO1640QDWRQ1	ISO6760QDWRQ1	ISO6731FQDWRQ1	ISO6760FQDWRQ
ISO6731QDWRQ1	ISO6761QDWRQ1	ISO6740FQDWRQ1	ISO6761FQDWRQ
ISO6740QDWRQ1	ISO6762QDWRQ1	ISO6741FQDWRQ1	ISO6762FQDWRQ
ISO6741QDWRQ1	ISO6763QDWRQ1	ISO6742FQDWRQ1	ISO6763FQDWRQ
ISO6742QDWRQ1			

Qualification Results Data Displayed as: Number of lots / Total sample size / Total failed

Туре	#	Test Spec	Min Lot Qty	SS/ Lot	Test Name / Condition	Duration	Qual Device: <u>SN3257QDYYRQ1</u>
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	Level 1-260C	No fails
HAST	A2	JEDEC JESD22- A110	3	77	Biased HAST, 130C/85%RH	96 Hours	3/231/0
AC	А3	JEDEC JESD22- A102	3	77	Autoclave 121C	96 Hours	3/231/0
тс	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle, -65/150C	500 Cycles	3/231/0
TC- WBP	A4	MIL-STD883 Method 2011	1	60	Bond Pull Post Temp Cycle	Wires	1/60/0
PTC	A5	JEDEC JESD22- A105	1	45	Power Temperature Cycle	1000 Cycles	N/A
HTSL	A6	JEDEC JESD22- A103	1	45	High Temp Storage Bake 150C	1000 Hours	3/135/0
		Test Group B -	- Accelera	ated Life	etime Simulation Tests		
HTOL	В1	JEDEC JESD22- A108	3	77	Life Test, 150C	300 Hours	3/231/0
ELFR	В2	AEC Q100-008	3	800	Early Life Failure Rate, 150C	24 Hours	3/2400/0
EDR	В3	AEC Q100-005	3	77	NVM Endurance, Data Retention, and Operational Life	-	N/A
		Test Group (C – Packa	ge Asse	mbly Integrity Tests		
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear Cpk >1.67	Wires	3/90/0

Туре	#	Test Spec	Min Lot Qty	SS/ Lot	Test Name / Condition	Duration	Qual Device: SN3257QDYYRQ1
WBP	C2	MIL-STD883 Method 2011	1	30	Bond Pull, Cpk >1.67	Wires	3/90/0
SD	С3	JEDEC JESD22- B102	1	15	Surface Mount Solderability	Pb Free Solder	1/15/0
SD	С3	JEDEC JESD22- B102	1	15	Surface Mount Solderability	Pb Solder	1/15/0
PD	C4	JEDEC JESD22- B100 and B108	3	10	Physical Dimensions	Cpk>1.67	3/30/0
		Test Group	D – Die F	abricati	on Reliability Tests		
EM	D1	JESD61	-	-	Electromigration	-	Completed Per Process Technology Requirements
TDDB	D2	JESD35	-	-	Time Dependant Dielectric Breakdown	-	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	-	-	Hot Injection Carrier	-	Completed Per Process Technology Requirements
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	Completed Per Process Technology Requirements
SM	D5	-	-	,	Stress Migration	-	Completed Per Process Technology Requirements
		Test Grou	ıp E – Ele	ctrical \	/erification Tests		
НВМ	E2	AEC Q100-002	1	3	ESD - HBM	2000 V	1/3/0
CDM	E3	AEC Q100-011	1	3	ESD - CDM	1500 V	1/3/0
LU	E4	AEC Q100-004	1	6	Latch-up	Per AEC Q100-004	1/6/0
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67	3/90/0

⁻ Qual Device SN3257QDYYRQ1 is qualified at LEVEL1-260C

A1 (PC): Preconditioning:

Performed for THB, Biased HAST, AC, uHAST, TC & PTC samples, as applicable.

Ambient Operating Temperature by Automotive Grade Level:

Grade 0 (or E): -40°C to +150°C Grade 1 (or Q): -40°C to +125°C Grade 2 (or T): -40°C to +105°C Grade 3 (or I): -40°C to +85°C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

Room/Hot/Cold : HTOL, ED

Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD $\&~{\rm LU}$

Room : AC/uHAST

Green/Pb-free Status:

Qualified Pb-Free(SMT) and Green

Qualification Results

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: UCC21520QDWRQ1	Qual Device: ISO5452DWR	QBS Reference: UCC21520QDWQ1	QBS Reference: ISO5851QDWQ1	QBS Reference: TMP451AQDQFRQ1	QBS Reference: AMC1305M25QDWQ1	QBS Reference: AMC1305M25QDWQ1
Test Group	A - Acce	elerated Enviror	nment St	ress Te:	sts									
PC	A1	JEDEC J- STD-020 JESD22- A113	3	77	Preconditioning	MSL1 260C		-		-	-	No Fails	-	
PC	A1	JEDEC J- STD-020 JESD22- A113	3	77	Preconditioning	MSL2 260C		No Fails	No Fails	No Fails	No Fails	-		-

PC	A1	JEDEC J- STD-020 JESD22- A113	3	77	Preconditioning	MSL3 260C	-		-	-	-		3/0/0	3/0/0
HAST	A2	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	96 Hours	-	1/77/0		3/231/0	3/231/0	3/231/0	3/231/0
AC/UHAST	А3	JEDEC JESD22- A102/JEDEC JESD22- A118	3	77	Autoclave	121C/15psig	96 Hours	-	1/77/0	1/77/0	1/77/0	3/231/0	3/231/0	3/231/0
тс	Д4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	1/77/0	1/77/0	1/77/0	1/77/0	3/231/0	3/231/0	3/231/0
TC-BP	Α4	MIL-STD883 Method 2011	1	5	Post Temp Cycle Bond Pull	-	-	1/5/0	1/5/0	-	-	1/5/0	1/5/0	1/5/0
HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	150C	1000 Hours	-	1/45/0		-		3/135/0	3/135/0
HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	175C	500 Hours	-	-	-	1/45/0	1/45/0	-	-
Test Group I	B - Agge	lerated Lifetime	: Simula	tion Test	ts									
HTOL	B1	JEDEC JESD22- A108	1	77	Life Test	125C	1000 Hours	-	-	-	3/231/0	-	-	-
HTOL	B1	JEDEC JESD22- A108	1	77	Life Test	150C	408 Hours	-	-	-	-	3/231/0	-	-
ELFR	B2	AEC Q100- 008	1	77	Early Life Failure Rate	125C	48 Hours	-	-	-	3/2400/0	-	-	-
ELFR	B2	AEC Q100- 008	1	77	Early Life Failure Rate	150C	24 Hours	-	-	-	-	3/2400/0	-	
Test Group (C - Pack	age Assembly	Integrity	Tests										
WBS	C1	AEC Q100- 001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cplo1.67	Wires	1/30/0	1/30/0	-	1/30/0	3/90/0	3/90/0	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	1/30/0	1/30/0	-	1/30/0	3/90/0	3/90/0	3/90/0
SD	СЗ	JEDEC J- STD-002	1	15	PB Solderability	>95% Lead Coverage	-		-	-	-		-	-
SD	СЗ	JEDEC J- STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	-	-	-	-	-	
PD	C4	JEDEC JESD22- B100 and B108	1	10	Physical Dimensions	Cpl>1.67		-		-	1/10/0	3/30/0		-
Test Group I	D - Die F	abrication Relia	sbility Te	sts										
ЕМ	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
нсі	D3	JESD60 & 28			Hot Carrier Injection			Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
NBTI	D4	-			Negative Bias Temperature Instability	-		Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
SM	D5	-			Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group	E - Elec	trical Verificatio	n Tests											
ESD	E2	AEC Q100- 002	1	3	ESD HBM	-	2000 Volts	Device specific data [1]	Device specific data [1]	1/3/0	1/3/0	1/3/0	-	-
ESD	E3	AEC Q100- 011	1	3	ESD CDM	-	500 Volts	Device specific data [1]	Device specific data [1]	1/3/0	1/3/0	1/3/0	-	-
LU	E4	AEC Q100- 004	1	6	Latch-Up	Per AEC Q100-004	-	Device specific data [1]	Device specific data [1]	1/6/0	1/6/0	1/6/0	-	-
ED	E5	AEC Q100- 009	3	30	Electrical Distributions	Cplc>1.67 Room, hot, and cold	-	1/30/0	1/30/0	1/30/0	1/30/0	3/90/0	3/90/0	3/90/0
Additional 1	lests:													
Туре	#	Test Spec	Min Lot Qty	SS/ Lot	Test Name	Condition	Duration	Qual Device	Qual Device	QBS Reference	QBS Reference	QBS Reference	QBS Reference	QBS Reference

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
 The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
 The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours
 The following are equivalent Temp Cycle options per JESD47: 55C/125C/700 Cycles and -55C/150C/500 Cycles

Ambient Operating Temperature by Automotive Grade Level:

- Grade 0 (or E): -40C to +150C
- Grade 1 (or Q): -40C to +125C
- Grade 2 (or T): -40C to +105C
- Grade 3 (or I): -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hol/Cold : HTOL, ED
 Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
 Room : AC/UHAST

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

TI Qualification ID: R-CHG-2203-108

[1] Qual Device: UCC21520QDWRQ1 and QBS Reference: UCC21520QDWQ1 use the same silicon die and bondout. Qual Device: ISO5452DWR and QBS Reference: ISO5851QDWQ1 use the same silicon die and bondout.

Qualification Results

Туре	#	Test Spec	Min Lot Qty	SS/ Lot	Test Name	Condition	Duration	Qual Device: AMC1305M25QDWQ1	Qual Device: AMC1305M25QDWQ1
Test G	roup A - A	Accelerated Environme	nt Stres	s Tests					
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL3 260C	1 Step	No Fails	No Fails
PC	A1.1	-	3	22	SAM Precon Pre	Review for delamination	1 Step	3/66/0	3/66/0
PC	A1.2	-	3	22	SAM Precon Post	Review for delamination	1 Step	3/66/0	3/66/0
HAST	A2.1	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	96 Hours	-	-
HAST	A2.1.2	-	3	1	Cross Section, post bHAST, 1X	Post stress cross section	Completed	-	-
HAST	A2.1.3	-	3	30	Wire Bond Shear, post bHAST, 1X	Post stress	Wires	-	-
HAST	A2.1.4	-	3	30	Bond Pull over Stitch, post bHAST, 1X	Post stress	Wires	-	-
HAST	A2.1.5	-	3	30	Bond Pull over Ball, post bHAST, 1X	Post stress	Wires	-	-
HAST	A2.2	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	192 Hours	3/231/0	3/231/0
HAST	A2.2.1	-	3	22	SAM Analysis, post bHAST 2X	Review for delamination	Completed	3/66/0	3/66/0
HAST	A2.2.2	-	3	1	Cross Section, post bHAST, 2X	Post stress cross section	Completed	3/3/0	3/3/0
HAST	A2.2.3	-	3	30	Wire Bond Shear, post bHAST, 2X	Post stress	Wires	3/9/0	3/9/0
HAST	A2.2.4	-	3	30	Bond Pull over Stitch, post bHAST, 2X	Post stress	Wires	3/9/0	3/9/0
HAST	A2.2.5	-	3	30	Bond Pull over Ball, post bHAST, 2X	Post stress	Wires	3/9/0	3/9/0
тс	A4.1	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	3/231/0	3/231/0
TC	A4.1.1	-	3	22	SAM Analysis, post TC 1X	Review for delamination	Completed	-	-
тс	A4.1.2	-	3	1	Cross Section, post TC, 1X	Post stress cross section	Completed	-	-
TC	A4.1.3	-	3	30	Wire Bond Shear, post TC, 1X	Post stress	Wires	-	-
тс	A4.1.4	-	3	30	Bond Pull over Stitch, post TC, 1X	Post stress	Wires	-	-
тс	A4.1.5	-	3	30	Bond Pull over Ball, post TC, 1X	Post stress	Wires	-	-
тс	A4.2	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	1000 Cycles	3/210/0	3/210/0
тс	A4.2.1	-	3	22	SAM Analysis, post TC, 2X	Review for delamination	Completed	3/66/0	3/66/0

тс	A4.2.2	-	3	1	Cross Section, post TC, 2X	Post stress cross section	Completed	3/3/0	3/3/0
тс	A4.2.3	-	3	30	Wire Bond Shear, post TC, 2X	Post stress	Wires	3/9/0	3/9/0
тс	A4.2.4	-	3	30	Bond Pull over Stitch, post TC, 2X	Post stress	Wires	3/9/0	3/9/0
тс	A4.2.5	-	3	30	Bond Pull over Ball, post TC, 2X	Post stress	Wires	3/9/0	3/9/0
HTSL	A6.1	JEDEC JESD22- A103	3	45	High Temperature Storage Life	150C	1000 Hours	3/135/0	3/135/0
HTSL	A6.1.1	-	3	1	Cross Section, post HTSL, 1X	Post stress cross section	Completed	-	-
HTSL	A6.2	JEDEC JESD22- A103	3	45	High Temperature Storage Life	150C	2000 Hours	3/132/0	3/132/0
HTSL	A6.2.1	-	3	1	Cross Section, post HTSL, 2X	Post stress cross section	Completed	3/3/0	3/3/0
Test Gr	roup B - A	Accelerated Lifetime Si	mulation	Tests					
Test Gr	roup C - F	ackage Assembly Inte	grity Tes	its					
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	3/90/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	3/90/0
SD	C3	JEDEC J-STD-002	1	15	PB Solderability	>95% Lead Coverage	-	-	-
SD	C3	JEDEC J-STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	-
PD	C4	JEDEC JESD22- B100 and B108	1	10	Physical Dimensions	Cpk>1.67	-	-	-
Test Gr	roup D - E)ie Fabrication Reliabili	ty Tests						
ЕМ	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
HCI	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements

Test Group E - Electrical Verification Tests

QBS: Qual By Similarity

SM

D5

- Qual Device AMC1305M25QDWQ1 is qualified at MSL3 260C
- Qual Device AMC1305M25QDWQ1 is qualified at MSL3 260C
- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours

Stress Migration

The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Ambient Operating Temperature by Automotive Grade Level:

- Grade 0 (or E): -40C to +150C
- Grade 1 (or Q): -40C to +125C
- Grade 2 (or T): -40C to +105C
- Grade 3 (or I) : -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold : HTOL, ED
- Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room : AC/uHAST

Quality and Environmental data is available at Tl's external Web site: http://www.ti.com/

Completed Per Process Technology Requirements

Completed Per Process

Technology Requirements

Automotive New Product Qualification Summary (As per AEC-Q100 and JEDEC Guidelines)

ISO67xxDW-Q1 and ISO164xDW-Q1 Full PCC Qual in TIM - Automotive Approve Date 20-June-2023

Product Attributes

Attributes	Qual Device:	QBS Reference:	QBS Reference:
Attributes	<u>ISO6763QDWRQ1</u>	<u>UCC23513QDWYQ1</u>	ISO6763QDWRQ1
Automotive Grade Level	Grade 1	Grade 1	Grade 1
Operating Temp Range (C)	-40 to 125	-40 to 125	-40 to 125
Product Function	Interface	Power Management	Interface
Wafer Fab Supplier	RFAB, RFAB	RFAB, RFAB	RFAB, RFAB
Assembly Site	MLA	TAI	MLA
Package Group	SOIC	SOIC	SOIC
Package Designator	DW	DWY	DW
Pin Count	16	6	16

- QBS: Qual By Similarity
- Qual Device ISO6763QDWRQ1 is qualified at MSL2 260C

Qualification Results

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: ISO6763QDWRQ1	QBS Reference: UCC23513QDWYQ1	QBS Reference: ISO6763QDWRQ1				
Test Group	Test Group A - Accelerated Environment Stress Tests													
PC	A1	JEDEC J-STD- 020 JESD22- A113	3	77	Preconditioning	MSL2 260C	-	No Fails	No Fails	No Fails				
HAST	A2	JEDEC JESD22- A110	3	77	Biased HAST	130C/85%RH	96 Hours	3/231/0	3/231/0	1/77/0				
AC/UHAST	A3	JEDEC JESD22- A102/JEDEC JESD22-A118	3	77	Autoclave	121C/15psig	96 Hours	3/231/0	3/231/0	1/77/0				
тс	A4	JEDEC JESD22- A104 and Appendix 3	3	77	Temperature Cycle	-65C/150C	500 Cycles	3/231/0	3/231/0	1/77/0				
TC-BP	A4	MIL-STD883 Method 2011	1	5	Post Temp Cycle Bond Pull	-	-	1/5/0	1/5/0	1/5/0				
HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	150C	1000 Hours	3/135/0	-	-				
HTSL	A6	JEDEC JESD22- A103	1	45	High Temperature Storage Life	175C	500 Hours	-	3/135/0	1/45/0				
Test Group	B - Acce	elerated Lifetime Sim	ulation 1	ests										
HTOL	B1	JEDEC JESD22- A108	1	77	Life Test	125C	1000 Hours	-	3/231/0	-				
ELFR	B2	AEC Q100-008	1	77	Early Life Failure Rate	125C	48 Hours	-	3/2400/0	-				
Test Group	C - Pack	age Assembly Integ	rity Test	s										
WBS	C1	AEC Q100-001	1	30	Wire Bond Shear	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	3/90/0	-				

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device	QBS Reference	QBS Reference
Additional	Tests									
ED	E5	AEC Q100-009	3	30	Electrical Distributions	Cpk>1.67 Room, hot, and cold	-	3/90/0	3/90/0	-
LU	E4	AEC Q100-004	1	6	Latch-Up	Per AEC Q100- 004	-	Device specific data [1]	1/6/0	1/6/0
ESD	E3	AEC Q100-011	1	3	ESD CDM	-	1500 Volts	Device specific data [1]	-	1/3/0
ESD	E2	AEC Q100-002	1	3	ESD HBM	-	2000 Volts	Device specific data [1]	-	1/3/0
Test Group	E - Elect	rical Verification Tes	ts							
SM	D5	-	-	-	Stress Migration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
NBTI	D4	-	-	-	Negative Bias Temperature Instability	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
нсі	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
TDDB	D2	JESD35	-	-	Time Dependent Dielectric Breakdown	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
ЕМ	D1	JESD61	-	-	Electromigration	-	-	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements	Completed Per Process Technology Requirements
Test Group	D - Die F	l abrication Reliability	/ Tests							
PD	C4	JEDEC JESD22- B100 and B108	1	10	Physical Dimensions	Cpk>1.67	-	-	3/30/0	
SD	C3	JEDEC J-STD- 002	1	15	PB-Free Solderability	>95% Lead Coverage	-	-	1/15/0	1/15/0
SD	C3	JEDEC J-STD- 002	1	15	PB Solderability	>95% Lead Coverage	-	-	1/15/0	1/15/0
WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull	Minimum of 5 devices, 30 wires Cpk>1.67	Wires	3/90/0	3/90/0	-

- Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV : 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47 : -55C/125C/700 Cycles and -65C/150C/500 Cycles

Orderable Part Numbers

The following table contains a list of all TI Orderable Part Numbers (OPNs) released by this qualification per Product Qualification Family definition (AEC Q100 Appendix 1). Group E results shown above cover all part numbers listed here.

ISO1640QDWRQ1	ISO6731FQDWRQ1
ISO6731QDWRQ1	ISO6740FQDWRQ1
ISO6740QDWRQ1	ISO6741FQDWRQ1
ISO6741QDWRQ1	ISO6742FQDWRQ1
ISO6742QDWRQ1	ISO6760FQDWRQ1
ISO6760QDWRQ1	ISO6761FQDWRQ1
ISO6761QDWRQ1	ISO6762FQDWRQ1
ISO6762QDWRQ1	ISO6763FQDWRQ1
ISO6763QDWRQ1	

Ambient Operating Temperature by Automotive Grade Level:

• Grade 0 (or E): -40C to +150C

- Grade 1 (or Q): -40C to +125C
- Grade 2 (or T): -40C to +105C
- Grade 3 (or I) : -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold : HTOL, ED
- Room/Hot : THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

TI Qualification ID: R-CHG-2203-118

[1] Qual Device: ISO6763QDWRQ1 and QBS Reference: ISO6763QDWRQ1 product use the same die sourced from the same Fab and use the same package and bondout. Change from hybrid Au and Cu wires to full Cu wire in assembly will not impact HBM, CDM, and LU result.

TI Information Selective Disclosure

Automotive New Product Qualification Summary (As per AEC-Q100, AEC-Q006, and JEDEC Guidelines)

Q006 report: 0.8mil Cu wire Qual in SOIC with CEL-8240HF-10GK at TIM Approve Date 20-June-2023

Qualification Results

Туре	#	Test Spec	Min Lot Qty	SS / Lot	Test Name	Condition	Duration	Qual Device: <u>ISO6763QDWRQ1</u>					
Test Gr	Test Group A - Accelerated Environment Stress Tests												
PC	A1	JEDEC J-STD-020 JESD22-A113	3	77	Preconditioning	MSL2 260C	-	No Fails					
PC	A1.1	-	3	22	SAM Precon Pre	Review for delamination	-	3/66/0					
PC	A1.2	-	3	22	SAM Precon Post	Review for delamination	-	3/66/0					
HAST	A2.1	JEDEC JESD22-A110	3	77	Biased HAST	130C/85%RH	96 Hours	3/231/0					
HAST	A2.1.2	-	3	1	Cross Section, post bHAST, 1X	Post stress cross section	Completed	-					
HAST	A2.1.3	-	3	30	Wire Bond Shear, post bHAST, 1X	Post stress	Wires	-					
HAST	A2.1.4	-	3	30	Bond Pull over Stitch, post bHAST, 1X	Post stress	Wires	-					

March Marc	HAST	A2.1.5	-	3	30	Bond Pull over Ball, post	Post stress	Wires	-
Marcia			IEDEC IESD22-A110	2	70	Bigged HAST	130C/95% PU		3/210/0
NAST A22 C. A24 A22 A24			JEDEC JESD22-A110						
Marcia M	HAST	A2.2.1	-	3	22	2X	Review for delamination	Completed	3/66/0
Part	HAST	A2.2.2	-	3	1		Post stress cross section	Completed	3/3/0
Marcia M	HAST	A2.2.3	-	3	30		Post stress	Wires	3/9/0
	HAST	A2.2.4	-	3	30		Post stress	Wires	3/9/0
	HAST	A2.2.5	-	3	30		Post stress	Wires	3/9/0
No.	тс	A4.1		3	77	Temperature Cycle	-65C/150C		3/231/0
National Content	TC	A4.1.1	-	3	22	SAM Analysis, post TC 1X	Review for delamination	Completed	-
National Content	TC	A4.1.2	-	3	1	Cross Section, post TC, 1X	Post stress cross section	Completed	-
	тс	A4.1.3	-	3	30		Post stress	Wires	-
The color	тс	A4.1.4	-	3	30		Post stress	Wires	-
Name	тс	A4.1.5	-	3	30		Post stress	Wires	-
TC A4.2.2	тс	A4.2		3	70	Temperature Cycle	-65C/150C		3/210/0
Name	TC	A4.2.1	-	3	22	SAM Analysis, post TC, 2X	Review for delamination	Completed	3/66/0
TC	TC	A4.2.2	-	3	1	Cross Section, post TC, 2X	Post stress cross section	Completed	3/3/0
Trace Trac	тс	A4.2.3	-	3	30		Post stress	Wires	3/9/0
HTSL A6.1 JEDEC JESD22-A103 3 45 High Temperature Storage 150C 1000 3/135/0 HTSL A6.1 - 3 1 Cross Section, post HTSL Post stress cross section Completed - HTSL A6.2 JEDEC JESD22-A103 3 44 High Temperature Storage 150C 2000 3/132/0 HTSL A6.2 JEDEC JESD22-A103 3 44 High Temperature Storage 150C 2000 3/132/0 HTSL A6.2 JEDEC JESD22-A103 3 44 High Temperature Storage 150C 2000 3/132/0 HTSL A6.2 JEDEC JESD22-A103 3 44 High Temperature Storage 150C 2000 3/132/0 HTSL A6.2 JEDEC JESD22-A103 3 44 High Temperature Storage 150C 2000 3/132/0 HTSL A6.2 JEDEC JESD22-A103 3 45 High Temperature Storage 150C 2000 3/132/0 HTSL A6.2 JEDEC JESD22-A103 3 45 High Temperature Storage 150C 2000 3/132/0 HTSL A6.2 JEDEC JESD22-A103 3 44 High Temperature Storage 150C 2000	тс	A4.2.4	-	3	30		Post stress	Wires	3/9/0
HTSL A6.1 - GEDEC JESD 22-A103 3 45 Life 1500 Hours 93.530 Hours 93.530 Hours 1500 Hours	тс	A4.2.5	-	3	30		Post stress	Wires	3/9/0
HTSL A6.2 JEDEC JESD22-A103 3	HTSL	A6.1	JEDEC JESD22-A103	3	45		150C		3/135/0
House Hous	HTSL	A6.1.1	-	3	1		Post stress cross section	Completed	-
Test Group B - Accelerated Lifetime Simulation Tests	HTSL	A6.2	JEDEC JESD22-A103	3	44		150C		3/132/0
Test Group C - Package Assembly Integrity Tests WBS C1 AEC Q100-001 1 30 Wire Bond Shear Minimum of 5 devices, 30 wires Cpk>1.67 Wires 3/90/0 WBP C2 MIL-STD883 Method 2011 1 30 Wire Bond Pull Minimum of 5 devices, 30 wires Cpk>1.67 Wires 3/90/0 SD C3 JEDEC J-STD-002 1 15 PB Solderability >95% Lead Coverage - - - SD C3 JEDEC J-STD-002 1 15 PB-Free Solderability >95% Lead Coverage - - - PD C4 JEDEC J-STD-002 1 15 PB-Free Solderability >95% Lead Coverage - - - PD C4 JEDEC J-STD-002 1 10 Physical Dimensions Cpk>1.67 - - - Test D-02 Jack Devices Jack De	HTSL	A6.2.1		3	1		Post stress cross section	Completed	3/3/0
WBS C1 AEC Q100-001 1 30 Wire Bond Shear Minimum of 5 devices, 30 wires Cpl>1.67 Wires 3/90/0 WBP C2 MIL-STD883 Method 2011 1 30 Wire Bond Pull Minimum of 5 devices, 30 wires Cpl>1.67 Wires 3/90/0 SD C3 JEDEC J-STD-002 1 15 PB Solderability >95% Lead Coverage - - PD C4 JEDEC J-STD-002 1 15 PB-Free Solderability >95% Lead Coverage - - PD C4 JEDEC J-STD-002 1 10 Physical Dimensions Cpk>1.67 - - Test Group J- Die Fabrication Reliability Tests EM D1 JESD61 - - Electromigration - - Completed Per Process Technology Requirements TDDB D2 JESD61 - - Hot Carrier Injection - - Completed Per Process Technology Requirements HCI D3 JESD60 & 28 - - Hot Carrier Injection - <td>Test G</td> <td>roup B - /</td> <td>Accelerated Lifetime Simulat</td> <td>ion Tests</td> <td></td> <td></td> <td></td> <td></td> <td></td>	Test G	roup B - /	Accelerated Lifetime Simulat	ion Tests					
WBP C1 AEC Q100-001 1 30 Wire Bond Shear wires Cpk>1.67 Wires 390/0 WBP C2 MIL-STD883 Method 2011 1 30 Wire Bond Pull Minimum of 5 devices, 30 wires Cpk>1.67 Wires 3/90/0 SD C3 JEDEC J-STD-002 1 15 PB Solderability >95% Lead Coverage - - PD C4 JEDEC J-STD-002 1 15 PB-Free Solderability >95% Lead Coverage - - PD C4 JEDEC J-STD-002 1 10 Physical Dimensions Cpk>1.67 - - Test Group D - Die Fabrication Reliability Tests EM D1 JESD61 - - Electromigration - - Completed Per Process Technology Requirements TDDB D2 JESD35 - - Time Dependent Dielectric Breakdown - - Completed Per Process Technology Requirements NBTI D4 - - - Negative Bias Temperature Instability -	Test G	roup C - F	Cackage Assembly Integrity	Tests					
SD C3 JEDEC J-STD-002 1 15 PB Solderability >95% Lead Coverage - - -	WBS	C1	AEC Q100-001	1	30	Wire Bond Shear		Wires	3/90/0
SD C3 JEDEC J-STD-002 1 15 PB-Free Solderability >95% Lead Coverage	WBP	C2	MIL-STD883 Method 2011	1	30	Wire Bond Pull		Wires	3/90/0
PD C4 JEDEC JESD22-B100 and B108	SD	С3	JEDEC J-STD-002	1	15	PB Solderability	>95% Lead Coverage	-	-
Test Group D - Die Fabrication Reliability Tests EM D1 JESD61 Electromigration - Completed Per Process Technology Requirements TDDB D2 JESD35 Time Dependent Dielectric Breakdown - Completed Per Process Technology Requirements HCI D3 JESD60 & 28 Hot Carrier Injection - Completed Per Process Technology Requirements NBTI D4 Stress Migration - Completed Per Process Technology Requirements SM D5 Stress Migration - Completed Per Process Technology Requirements	SD	С3	JEDEC J-STD-002	1	15	PB-Free Solderability	>95% Lead Coverage	-	-
EM D1 JESD61 - - Electromigration - - Completed Per Process Technology Requirements TDDB D2 JESD35 - - Time Dependent Dielectric Breakdown - - Completed Per Process Technology Requirements HCI D3 JESD60 & 28 - - Hot Carrier Injection - - Completed Per Process Technology Requirements NBTI D4 - - - Negative Bias Temperature Instability - - Completed Per Process Technology Requirements SM D5 - - Stress Migration - - Completed Per Process Technology Requirements	PD	C4		1	10	Physical Dimensions	Cpk>1.67	-	-
TDDB D2 JESD35 - Time Dependent Dielectric Breakdown - Completed Per Process Technology Requirements HCI D3 JESD60 & 28 - Hot Carrier Injection - Completed Per Process Technology Requirements NBTI D4 - Negative Bias Temperature Instability - Completed Per Process Technology Requirements SM D5 - Stress Migration - Stress Migration - Completed Per Process Technology Requirements	Test G	roup D - [Die Fabrication Reliability Tes	its					
HCI D3 JESD60 & 28 - Hot Carrier Injection - Completed Per Process Technology Requirements NBTI D4 - Negative Bias Temperature Instability - Completed Per Process Technology Requirements SM D5 - Stress Migration - Stress Migration - Completed Per Process Technology Requirements - Completed Per Process Technology Requirements - Completed Per Process Technology Requirements	EM	D1	JESD61	-	-	Electromigration	-	-	
NBTI D4 - Negative Bias Temperature Instability - Completed Per Process Technology Requirements NBTI D5 - Stress Migration - Stress Migration - Completed Per Process Technology Requirements	TDDB	D2	JESD35	-	-		-	-	
SM D5 - Stress Migration - Technology Requirements Small D5 - Stress Migration - Completed Per Process Technology Requirements	нсі	D3	JESD60 & 28	-	-	Hot Carrier Injection	-	-	
Technology Requirements	NBTI	D4	-	-	-		-	-	
Test Group E - Electrical Verification Tests	SM	D5	-	-	-	Stress Migration	-	-	
	Test G	roup E - E	Electrical Verification Tests						

- QBS: Qual By Similarity
 Qual Device ISO6763QDWRQ1 is qualified at MSL2 260C

- · Preconditioning was performed for Autoclave, Unbiased HAST, THB/Biased HAST, Temperature Cycle, Thermal Shock, and HTSL, as applicable
- The following are equivalent HTOL options based on an activation energy of 0.7eV: 125C/1k Hours, 140C/480 Hours, 150C/300 Hours, and 155C/240 Hours
- The following are equivalent HTSL options based on an activation energy of 0.7eV: 150C/1k Hours, and 170C/420 Hours
- The following are equivalent Temp Cycle options per JESD47: -55C/125C/700 Cycles and -65C/150C/500 Cycles

Ambient Operating Temperature by Automotive Grade Level:

- Grade 0 (or E): -40C to +150C
- Grade 1 (or Q): -40C to +125C
- Grade 2 (or T): -40C to +105C
- Grade 3 (or I) : -40C to +85C

E1 (TEST): Electrical test temperatures of Qual samples (High temperature according to Grade level):

- Room/Hot/Cold : HTOLED
- Room/Hot: THB / HAST, TC / PTC, HTSL, ELFR, ESD & LU
- Room : AC/uHAST

Quality and Environmental data is available at TI's external Web site: http://www.ti.com/

TI Qualification ID: R-CHG-2203-118

Affected ZVEI IDs: SEM-PW-02, SEM-PW-13, SEM-PA-08, SEM-PS-03

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